

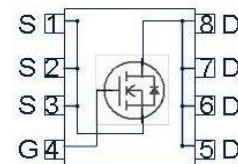
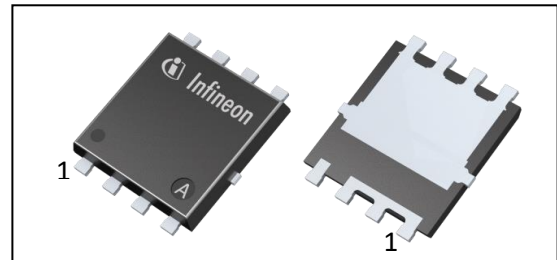
**OptiMOS™ -5 Power Transistor**

**Features**

- OptiMOS™ power MOSFET for automotive applications
- N-channel - Enhancement mode - Logic Level
- MSL1 up to 260°C peak reflow
- 175 °C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

**Product Summary**

$V_{DS}$	60	V
$R_{DS(on),max}$	10	mΩ
$I_D$	41	A

**PG-TDSON-8-33**


Type	Package	Marking
IAUC41N06S5L100	<a href="#">PG-TDSON-8-33</a>	5N06L100

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Drain current	$I_D$	$V_{GS}=10\text{ V}$ , Chip limitation <sup>1,2)</sup>	41	A
		$V_{GS}=10\text{V}$ , DC current	41	
		$T_a=85\text{ °C}$ , $V_{GS}=10\text{ V}$ , $R_{thJA}$ on 2s2p <sup>2,3)</sup>	12	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$ , $t_p=100\text{ }\mu\text{s}$	115	
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	$I_D=20\text{ A}$	37	mJ
Avalanche current, single pulse	$I_{AS}$	-	41	A
Gate source voltage	$V_{GS}$	-	±16	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	42	W
Operating and storage temperature	$T_j, T_{stg}$	-	-55 ... +175	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics<sup>2)</sup>**

Thermal resistance, junction - case	$R_{thJC}$	-	-	-	3.6	K/W
Thermal resistance, junction - ambient <sup>3)</sup>	$R_{thJA}$	-	-	25.5	-	

**Electrical characteristics, at  $T_j=25^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	60	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=13\mu A$	1.2	1.7	2.2	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	-	1	$\mu A$
		$V_{DS}=60V, V_{GS}=0V, T_j=125^\circ\text{C}^{1)}$	-	-	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=16V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=20A$	-	11.6	13.9	$m\Omega$
		$V_{GS}=10V, I_D=20A$	-	7.9	10	
Gate resistance <sup>2)</sup>	$R_G$	-	-	1.1	-	$\Omega$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>2)</sup>**

Input capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=30V,$ $f=1MHz$	-	927	1205	pF
Output capacitance	$C_{oss}$		-	183	238	
Reverse transfer capacitance	$C_{rss}$		-	12	18	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30V, V_{GS}=10V,$ $I_D=20A, R_{G,ext}=3.5\Omega$	-	2.4	-	ns
Turn-off delay time	$t_{d(off)}$		-	6.7	-	
Rise time	$t_r$		-	1.0	-	
Fall time	$t_f$		-	2.2	-	

**Gate Charge Characteristics<sup>2)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=30V, I_D=20A,$ $V_{GS}=0$ to 10V	-	3.0	4.0	nC
Gate to drain charge	$Q_{gd}$		-	2.1	3.1	
Gate charge total	$Q_g$		-	12.7	16.4	
Gate plateau voltage	$V_{plateau}$		-	3.3	-	V

**Reverse Diode**

Diode continuous forward current <sup>2)</sup>	$I_S$	$T_C=25^\circ C$	-	-	41	A
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	$T_C=25^\circ C, t_p=100\mu s$	-	-	115	
Diode forward voltage	$V_{SD}$	$V_{GS}=0V, I_F=20A,$ $T_j=25^\circ C$	-	0.8	1.1	V
Reverse recovery time <sup>2)</sup>	$t_{rr}$	$V_R=30V, I_F=41A,$ $di_F/dt=100A/\mu s$	-	26	-	ns
Reverse recovery charge <sup>2)</sup>	$Q_{rr}$		-	16	-	nC

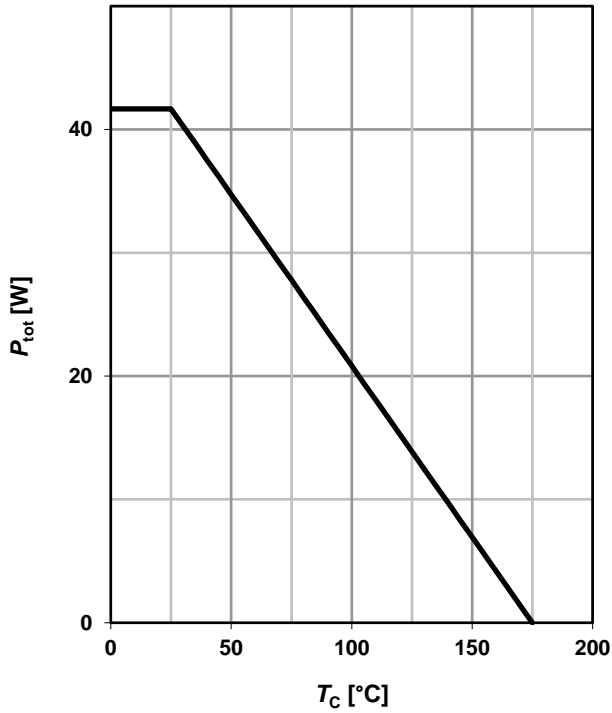
<sup>1)</sup> Practically the current is limited by the overall system design including the customer-specific PCB.

<sup>2)</sup> The parameter is not subject to production test - verified by design/characterization.

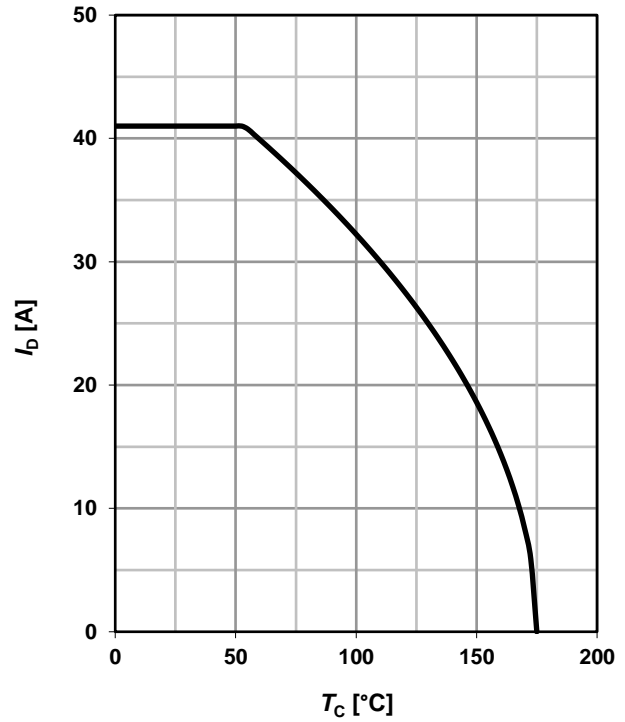
<sup>3)</sup> Device on a four-layer 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5-7). PCB is vertical in still air.

**1 Power dissipation**

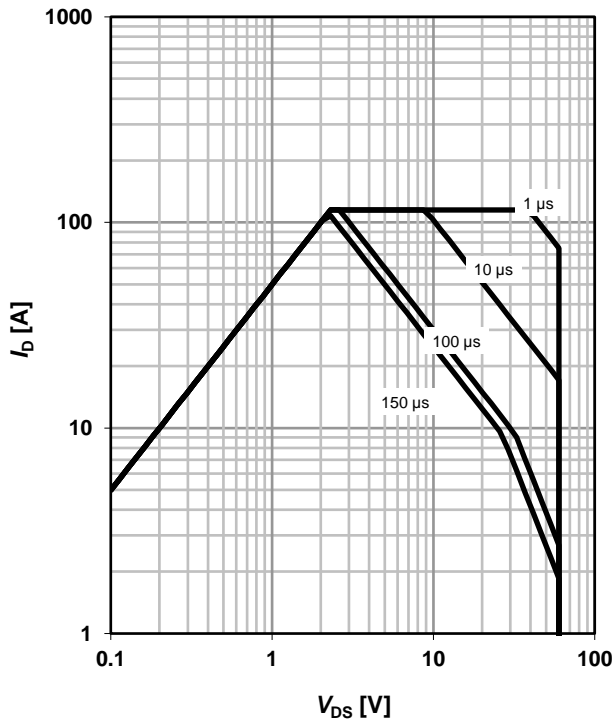
$$P_{\text{tot}} = f(T_C); V_{\text{GS}} = 10 \text{ V}$$


**2 Drain current**

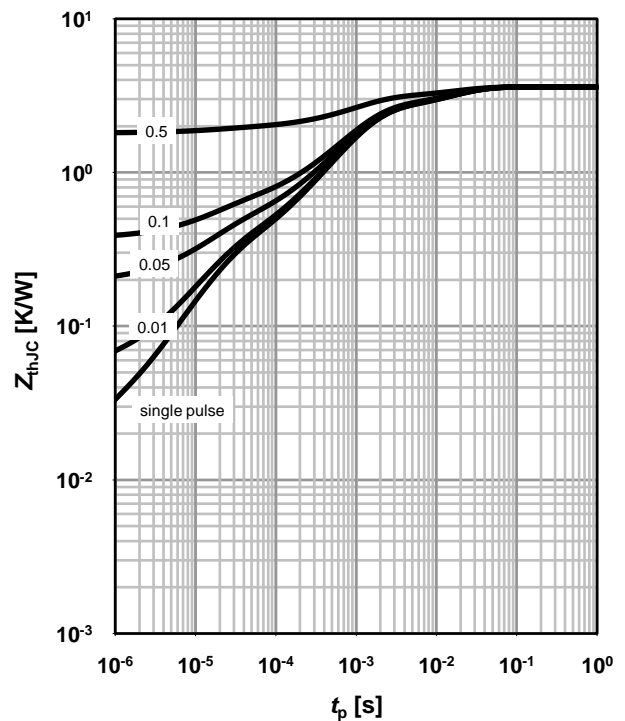
$$I_D = f(T_C); V_{\text{GS}} = 10 \text{ V}$$


**3 Safe operating area**

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0$$

 parameter:  $t_p$ 

**4 Max. transient thermal impedance**

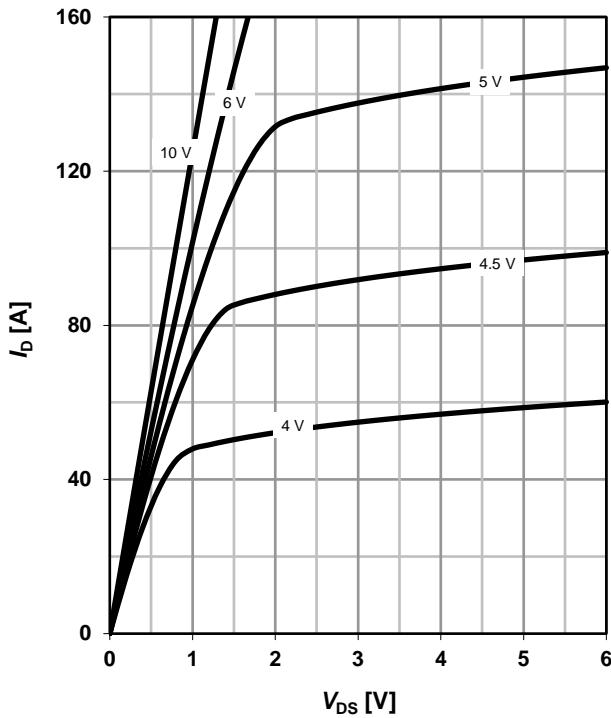
$$Z_{\text{thJC}} = f(t_p)$$

 parameter:  $D = t_p/T$ 


**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

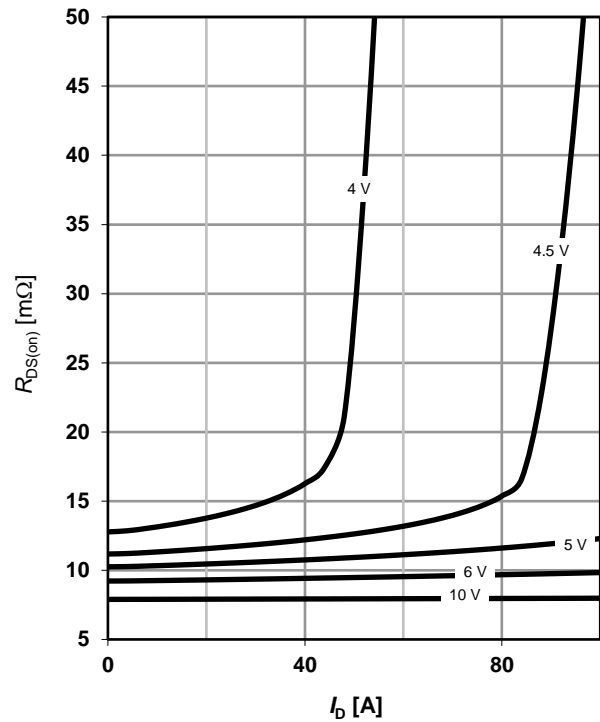
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

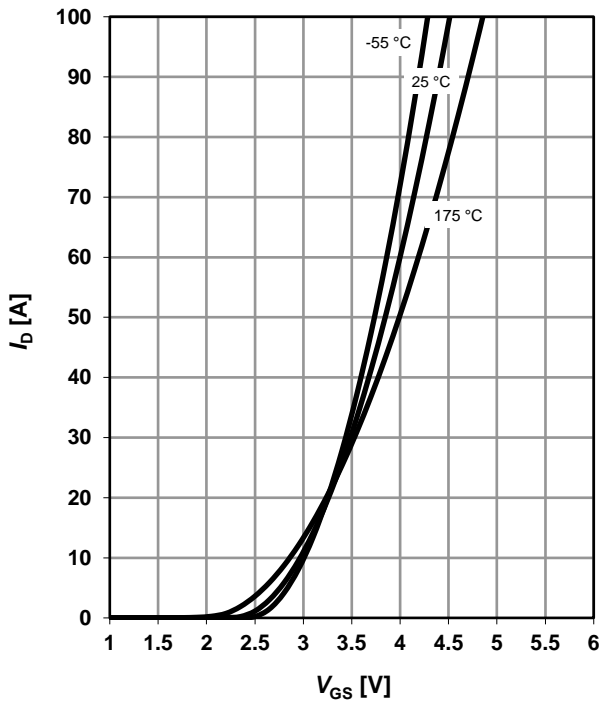
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

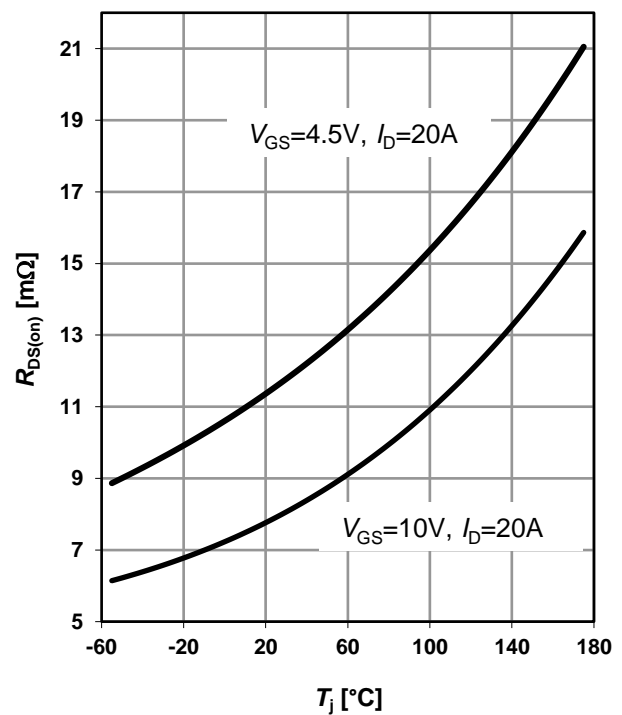
parameter:  $T_j$



**8 Typ. drain-source on-state resistance**

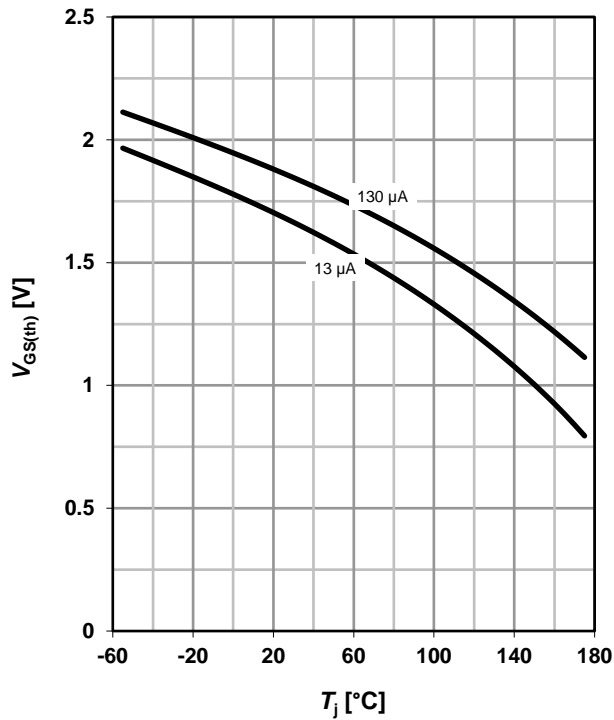
$R_{DS(on)} = f(T_j);$

parameter:  $I_D, V_{GS}$

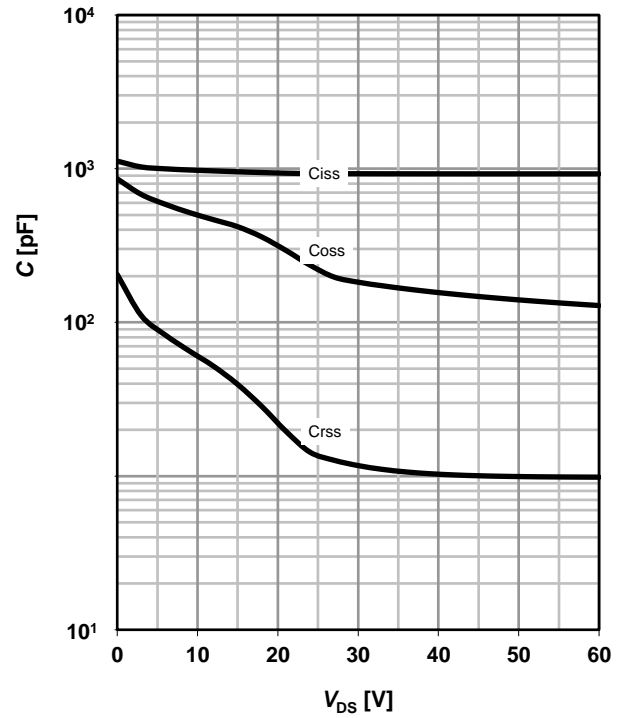


**9 Typ. gate threshold voltage**

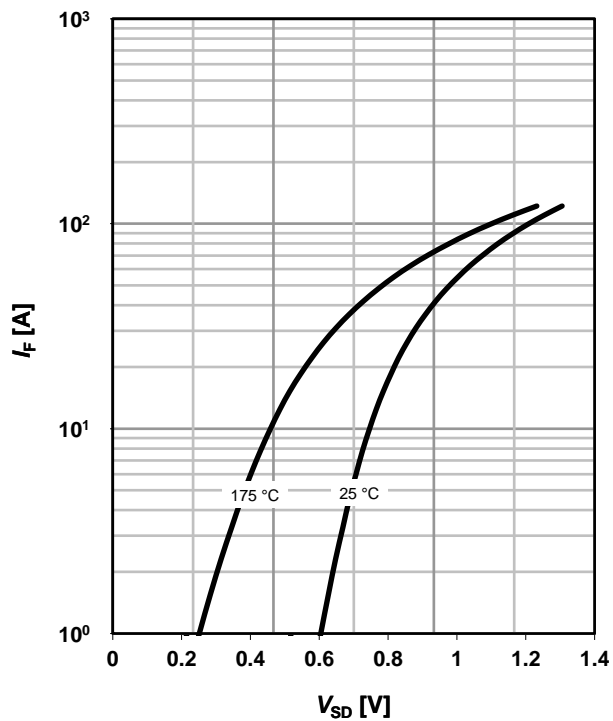
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

 parameter:  $I_D$ 

**10 Typ. capacitances**

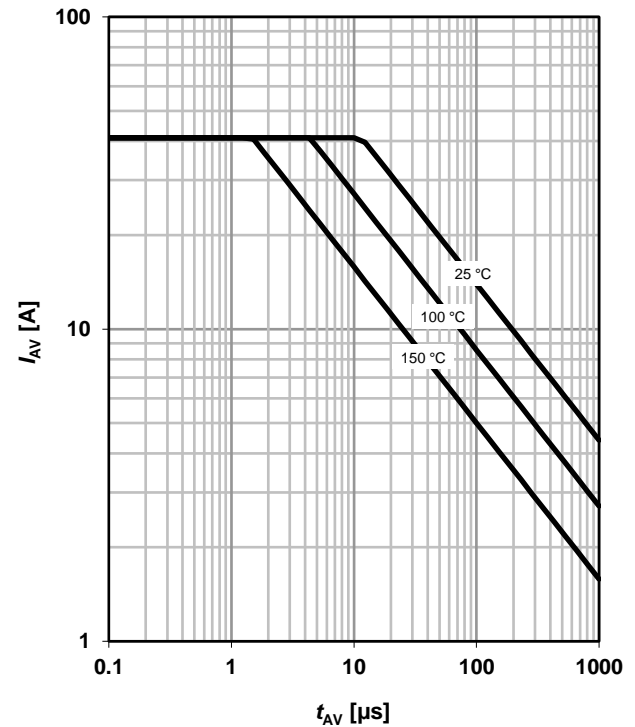
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$


**11 Typical forward diode characteristics**

$$I_F = f(V_{SD})$$

 parameter:  $T_j$ 

**12 Avalanche characteristics**

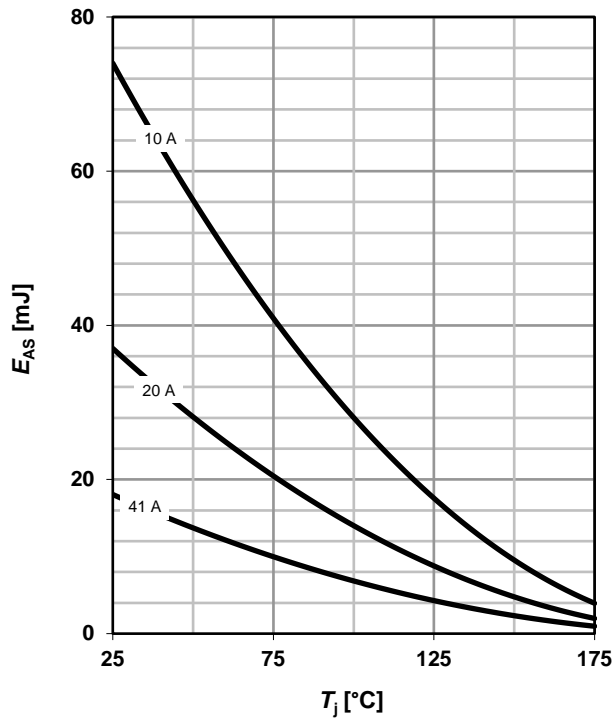
$$I_{AS} = f(t_{AV})$$

 parameter:  $T_{j(start)}$ 


### 13 Avalanche energy

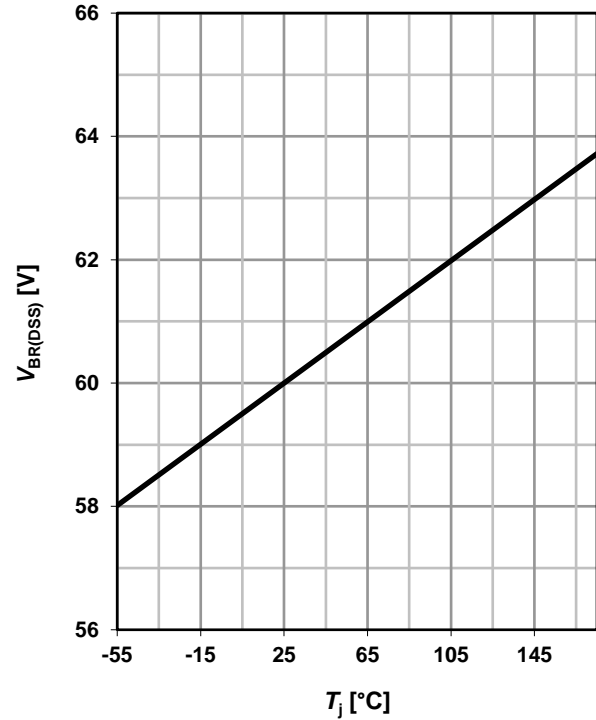
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



### 14 Drain-source breakdown voltage

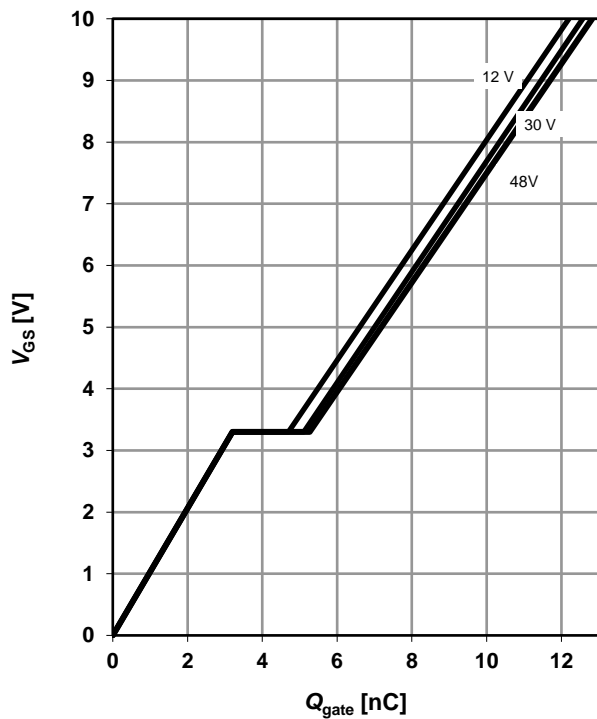
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



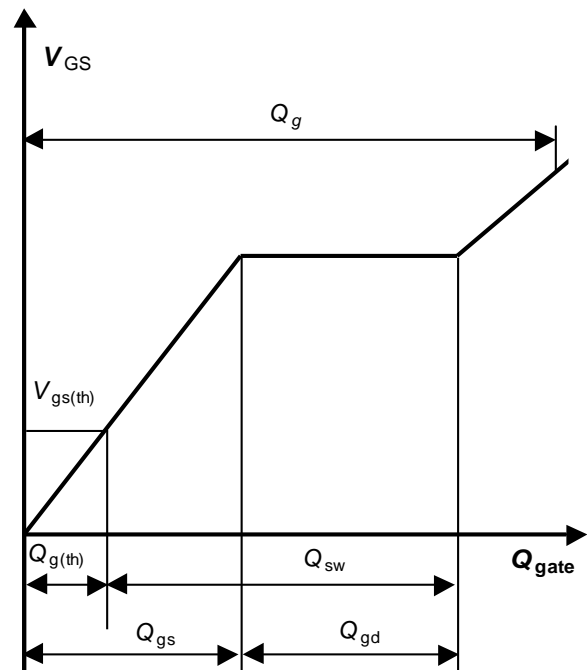
### 15 Typ. gate charge

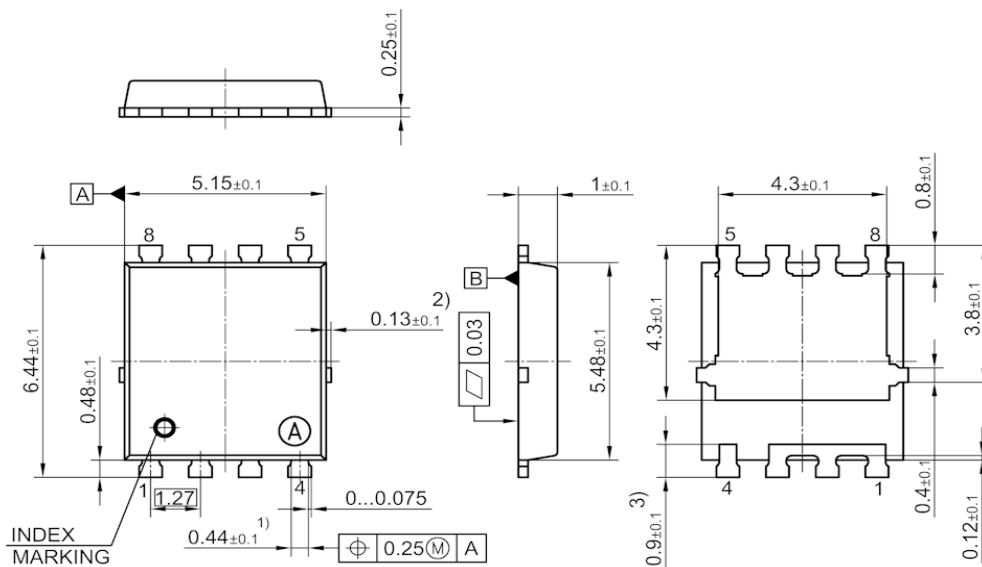
$$V_{GS} = f(Q_{gate}); I_D = 20 \text{ A pulsed}$$

parameter:  $V_{DD}$

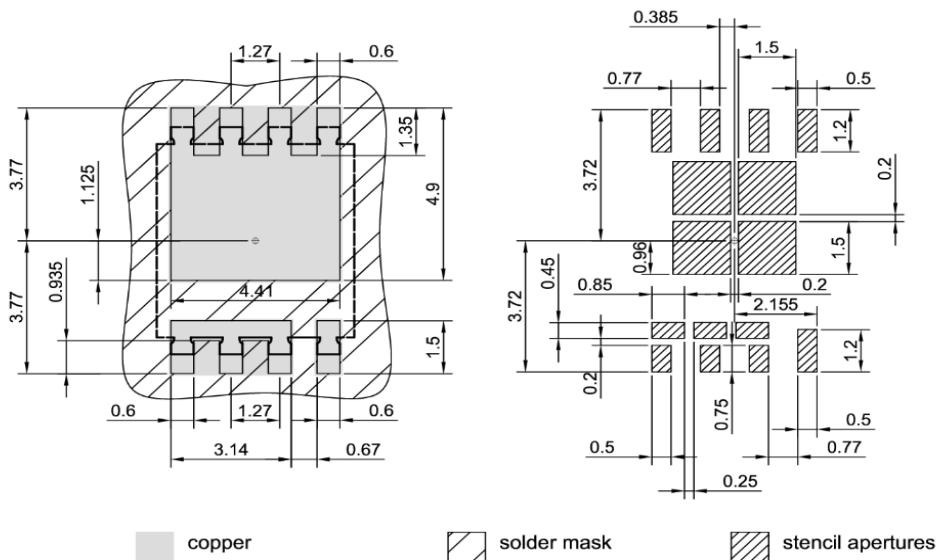


### 16 Gate charge waveforms

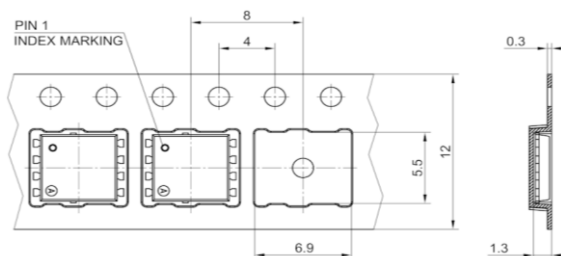


**Package Outline**


- 1) EXCLUDE MOLD FLASH
  - 2) REMOVAL ON MOLD GATE, INTRUSION 0.1MM AND PROTRUSION 0.1MM
  - 3) LEAD LENGTH UP TO ANTI FLASH LINE
  - 4) ALL METAL SURFACE ARE PLATED, EXCEPT AREA OF CUT
- ALL DIMENSIONS ARE IN UNITS MM  
 THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 [ ]

**Footprint**


All dimensions are in units mm

**Packaging**




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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

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Revision History

Version	Date	Changes
Revision 1.0	05.05.2020	Final Data Sheet